



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Sheu, et al. Docket No.: TSM03-0140
Serial No.: 10/619,828 Art Unit: 2811
Filed: July 15, 2003 Examiner: TBD
For: Self-Aligned MOSFET having an Oxide Region below the Channel

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Information Disclosure Statement (1 page)
IDS Forms PTO/SB/08a and 08b (3 pages) citing (41) references
Copies of (24) cited references
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Respectfully submitted,

Natalie Swider
Legal Assistant

Slater & Matsil, L.L.P.
17950 Preston Rd., Suite 1000
Dallas, TX 75252
Tel: 972-732-1001
Fax: 972-732-9218



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Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

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No fee is due at this time, as this Information Disclosure Statement is being filed pursuant to 37 C.F.R. § 1.97(b)(3), before the mailing of a first Office action on the merits.

Respectfully submitted,

25 MAR 2004

Date



Steven H. Slater
Attorney for Applicants
Reg. No. 35,361

Slater & Matsil, L.L.P.
17950 Preston Rd., Suite 1000
Dallas, TX 75252
(972) 732-1001 (phone)
(972) 732-9218 (fax)



PTO/SB/08A (02-03)

Approved for use through 4/30/2003. OMB 0651-0031

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<i>Complete if Known</i>	
Application Number	10/619,828
Filing Date	07/15/2003
First Named Inventor	Sheu, et al.
Art Unit	2811
Examiner Name	TBD
Attorney Docket Number	TSM03-0140

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

Examiner Signature		Date Considered	
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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	18	ISMAIL, K., et al., "Electron Transport Properties of Si/SiGe Heterostructures: Measurements and Device Implications," Applied Physics Letters, Vol. 63, No. 5, (August 2, 1993), pp. 660-662.	
	19	NAYAK, D.K., et al., "Enhancement-Mode Quantum-Well Ge _x Si _{1-x} PMOS," IEEE Electron Device Letters, Vol. 12, No. 4, (April 1991), pp. 154-156.	
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	21	GAMIZ, F., et al., "Electron Transport in Strained Si Inversion Layers Grown on SiGe-on-Insulator Substrates," Journal of Applied Physics, Vol. 92, No. 1, (July 1, 2002), pp. 288-295.	
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	27	TIWARI, S., et al., "Hole Mobility Improvement in Silicon-on-Insulator and Bulk Silicon Transistors Using Local Strain," International Electron Device Meeting, (1997), pp.939-941.	
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	31	MATTHEWS, J.W., et al., "Defects in Epitaxial Multilayers – III. Preparation of Almost Perfect Multilayers," Journal of Crystal Growth, Vol. 32, (1976), pp. 265-273.	
	32	SCHÜPPEN, A., et al., "Mesa and Planar SiGe-HBTs on MBE-Wafers," Journal of Materials Science: Materials in Electronics, Vol. 6, (1995), pp. 298-305.	
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